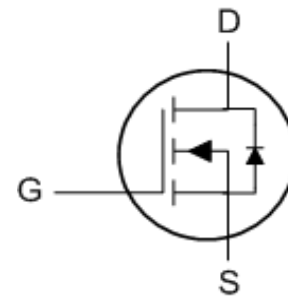




- ★ Green Device Available
- ★ Super Low Gate Charge
- ★ Excellent CdV/dt effect decline
- ★ Advanced high cell density Trench technology

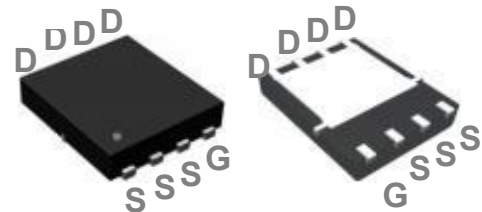


### Description

The WLQ032R04F is the high cell density trenched N-ch MOSFETs, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications.

The WLQ032R04F meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

### PDFN5060-8L Pin Configuration



### Product Summary

BVDSS	RDSON	ID
40V	2.7 mΩ	54 A

### Absolute Maximum Ratings (@ T<sub>C</sub> = 25°C unless otherwise specified)

Symbol	Parameter	Value	Units
V <sub>DS</sub>	Drain-to-Source Voltage	40	V
V <sub>GS</sub>	Gate-to-Source Voltage	±20	V
I <sub>D</sub>	Continuous Drain Current	T <sub>C</sub> = 25°C	54
		T <sub>C</sub> = 100°C	50
I <sub>DM</sub>	Pulsed Drain Current <sup>(1)</sup>	320	A
E <sub>AS</sub>	Single Pulsed Avalanche Energy <sup>(2)</sup>	156	mJ
P <sub>D</sub>	Power Dissipation	T <sub>C</sub> = 25°C	142
R <sub>θJA</sub>	Thermal Resistance, Junction to Ambient <sup>(3)</sup>	31	°C/W
R <sub>θJC</sub>	Thermal Resistance, Junction to Case	0.88	
T <sub>J</sub> , T <sub>STG</sub>	Junction & Storage Temperature Range	-55 to 150	°C



### Electrical Characteristics (T<sub>J</sub> = 25°C unless otherwise specified)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
<b>Off Characteristics</b>						
V <sub>(BR)DSS</sub>	Drain-Source Breakdown Voltage	I <sub>D</sub> = 250μA, V <sub>GS</sub> = 0V	40	-	-	V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> = 40V, V <sub>GS</sub> = 0V	-	-	1.0	μA
I <sub>GSS</sub>	Gate-Body Leakage Current	V <sub>DS</sub> = 0V, V <sub>GS</sub> = ±20V	-	-	±100	nA
<b>On Characteristics</b>						
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA	1.0	-	2.5	V
R <sub>DS(ON)</sub>	Static Drain-Source ON-Resistance <sup>(4)</sup>	V <sub>GS</sub> = 10V, I <sub>D</sub> = 30A	-	2	2.7	mΩ
		V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 20A	-	3.3	4.8	mΩ
<b>Dynamic Characteristics</b>						
C <sub>iss</sub>	Input Capacitance	V <sub>GS</sub> = 0V, V <sub>DS</sub> = 20V, f = 1MHz	-	3778	-	pF
C <sub>oss</sub>	Output Capacitance		-	267	-	pF
C <sub>rss</sub>	Reverse Transfer Capacitance		-	224	-	pF
Q <sub>g</sub>	Total Gate Charge	V <sub>GS</sub> = 0 to 10V V <sub>DS</sub> = 20V, I <sub>D</sub> = 30A	-	73	-	nC
Q <sub>gs</sub>	Gate Source Charge		-	15	-	nC
Q <sub>gd</sub>	Gate Drain ("Miller") Charge		-	16	-	nC
<b>Switching Characteristics</b>						
t <sub>d(on)</sub>	Turn-On DelayTime	V <sub>GS</sub> = 10V, V <sub>DD</sub> = 20V I <sub>D</sub> = 30A, R <sub>GEN</sub> = 3Ω	-	12	-	ns
t <sub>r</sub>	Turn-On Rise Time		-	29	-	ns
t <sub>d(off)</sub>	Turn-Off DelayTime		-	60	-	ns
t <sub>f</sub>	Turn-Off Fall Time		-	16	-	ns
<b>Drain-Source Diode Characteristics and Max Ratings</b>						
I <sub>S</sub>	Maximum Continuous Drain to Source Diode Forward Current		-	-	100	A
I <sub>SM</sub>	Maximum Pulsed Drain to Source Diode Forward Current		-	-	320	A
V <sub>SD</sub>	Drain to Source Diode Forward Voltage	V <sub>GS</sub> = 0V, I <sub>S</sub> = 30A	-	-	1.2	V
t <sub>rr</sub>	Body Diode Reverse Recovery Time	I <sub>F</sub> = 20A, di/dt = 100A/us	-	16	-	ns
Q <sub>rr</sub>	Body Diode Reverse Recovery Charge		-	10	-	nC

- Notes:
1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature.
  2. E<sub>AS</sub> condition: Starting T<sub>J</sub>=25C, V<sub>DD</sub>=20V, V<sub>G</sub>=10V, R<sub>G</sub>=25ohm, L=0.5mH, I<sub>AS</sub>=25A
  3. R<sub>θJA</sub> is measured with the device mounted on a 1inch<sup>2</sup> pad of 2oz copper FR4 PCB
  4. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 0.5%.



### Typical Performance

Figure 1: Output Characteristics

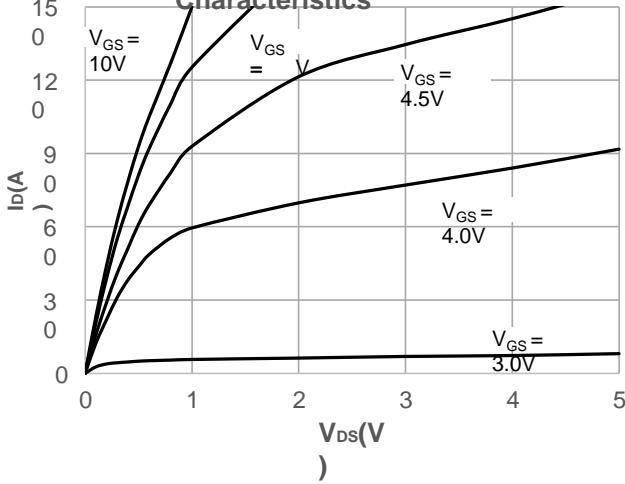


Figure 2: Typical Transfer Characteristics

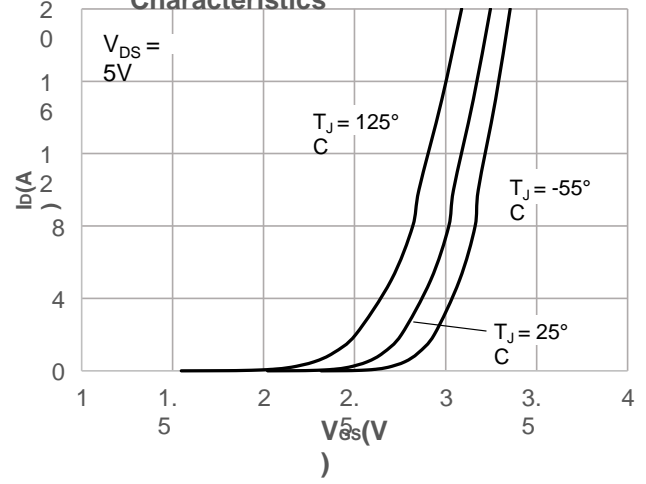


Figure 3: On-resistance vs. Drain Current

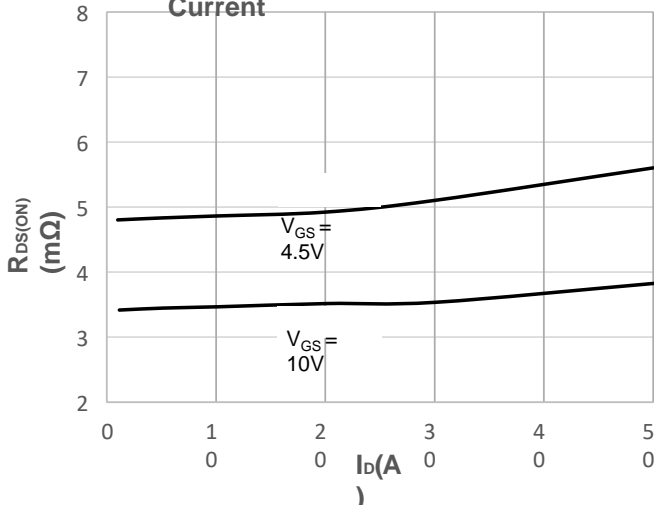


Figure 4: Body Diode Characteristics

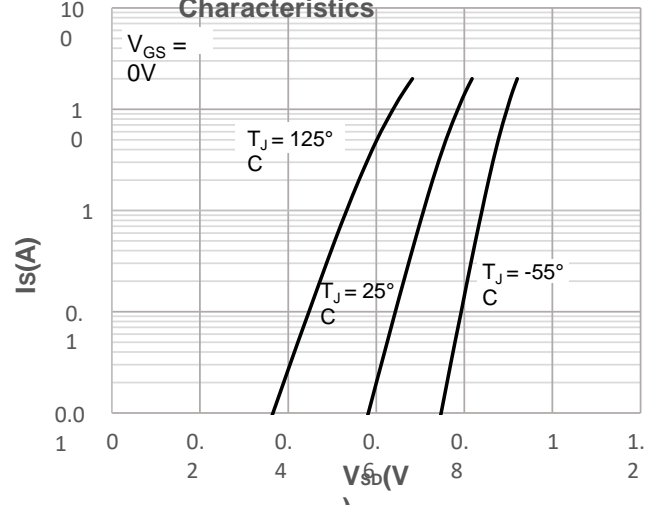


Figure 5: Gate Charge Characteristics

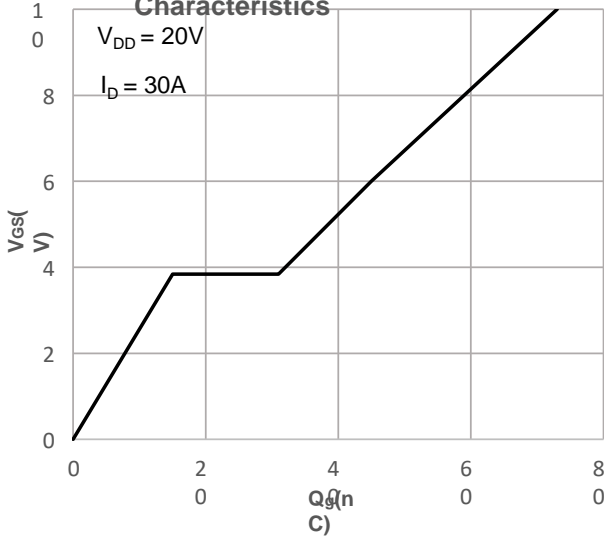
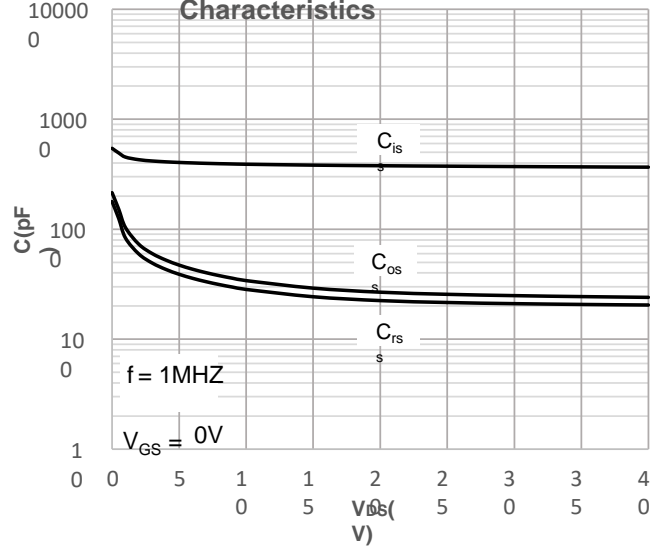


Figure 6: Capacitance Characteristics





### Typical Performance

Figure 7: Normalized Breakdown voltage vs. Junction Temperature

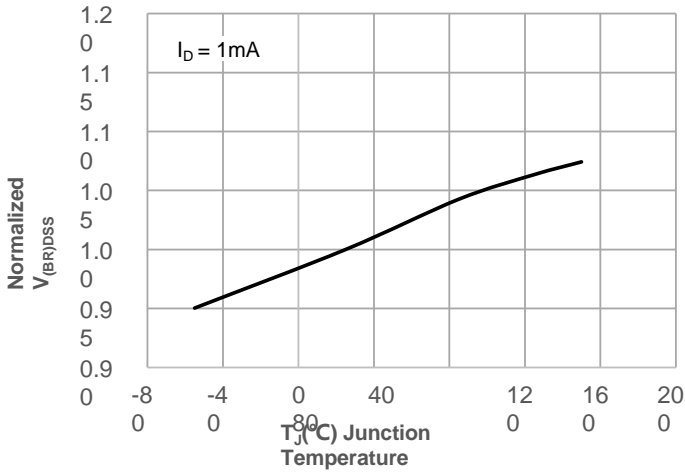


Figure 8: Normalized on Resistance vs. Junction Temperature

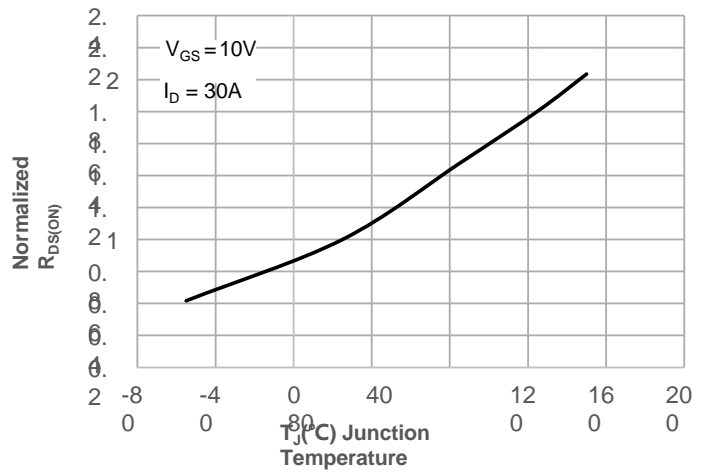


Figure 9: Maximum Safe Operating Area

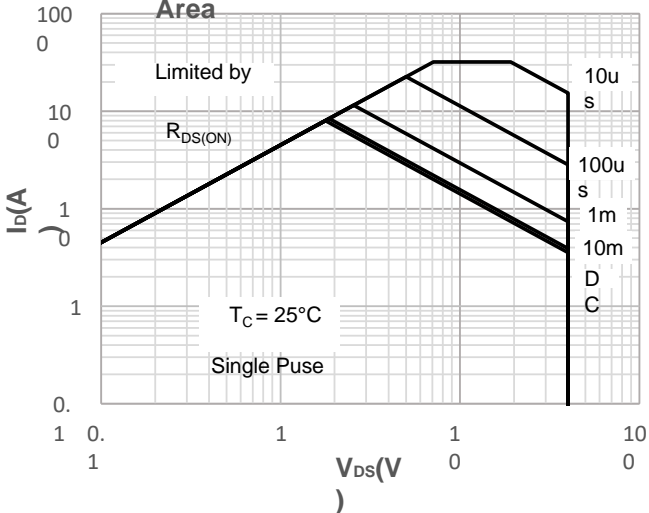


Figure 10: Maximum Continuous Drianc Current vs. Case Temperature

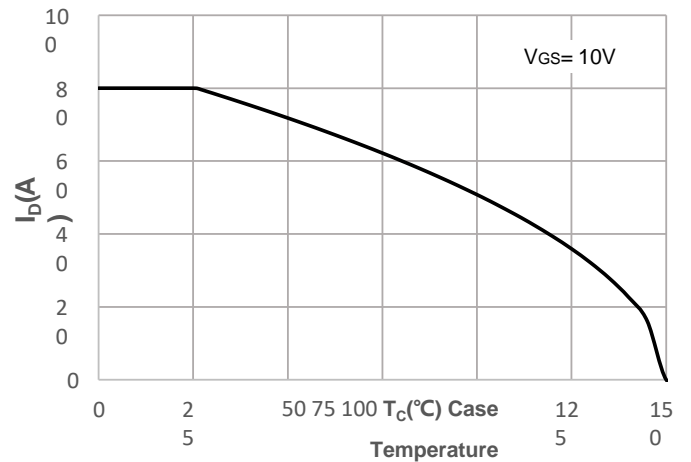


Figure 11: Normalized Maximum Transient Thermal Impedance

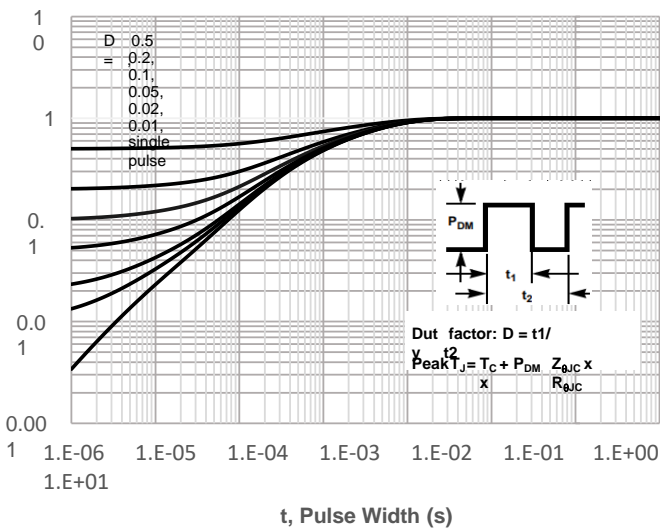
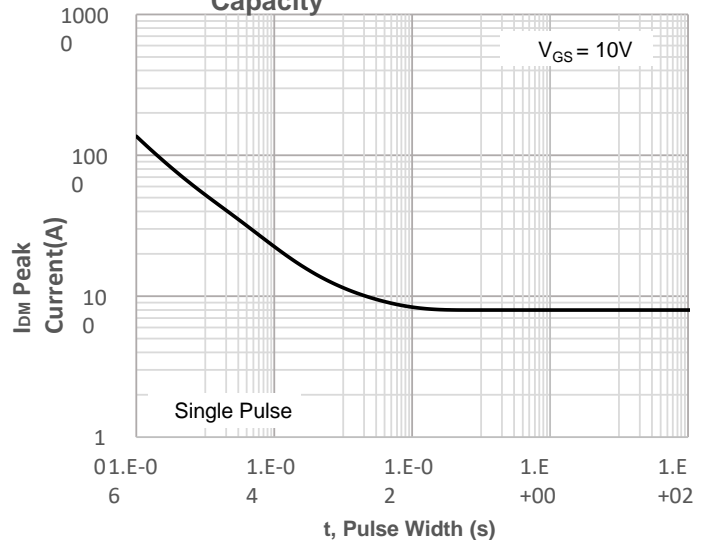


Figure 12: Peak Current Capacity





### Test Circuit

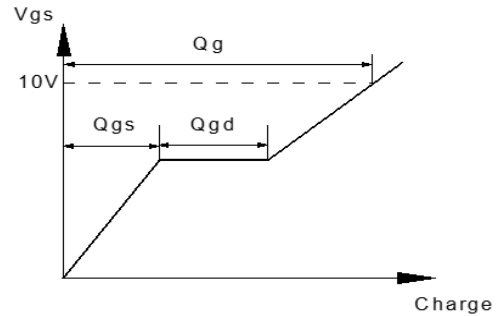
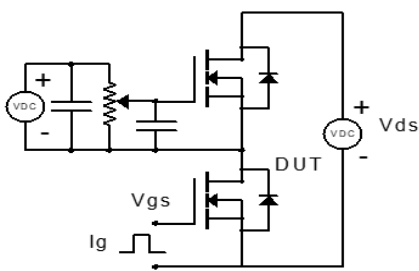


Figure 1: Gate Charge Test Circuit & Waveform

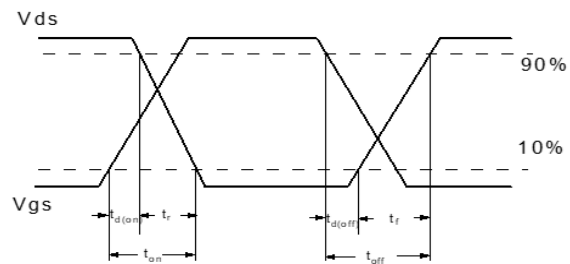
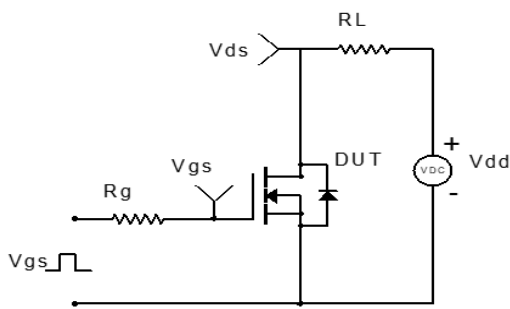


Figure 2: Resistive Switching Test Circuit & Waveform

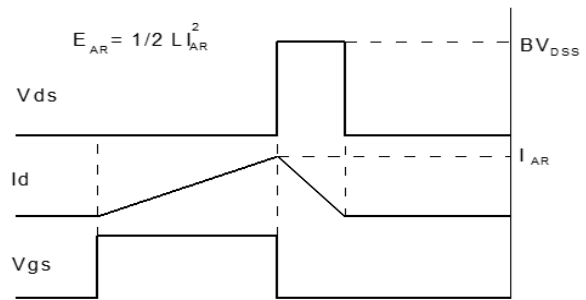
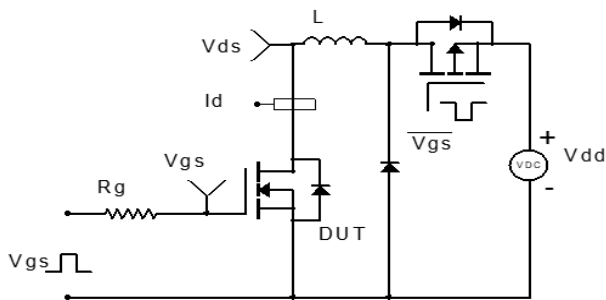


Figure 3: Unclamped Inductive Switching Test Circuit & Waveform

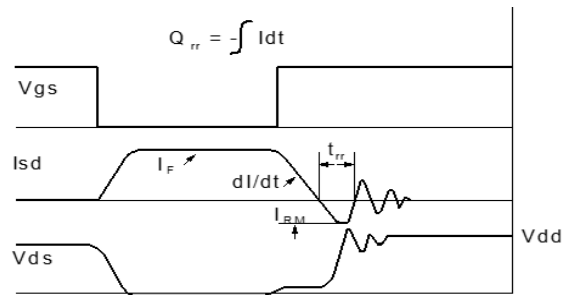
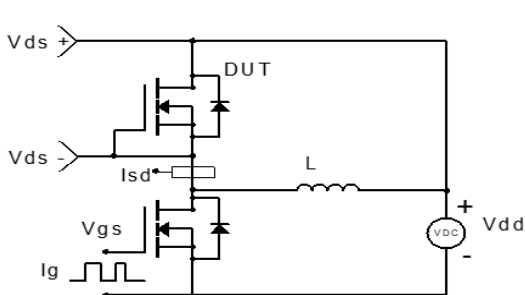
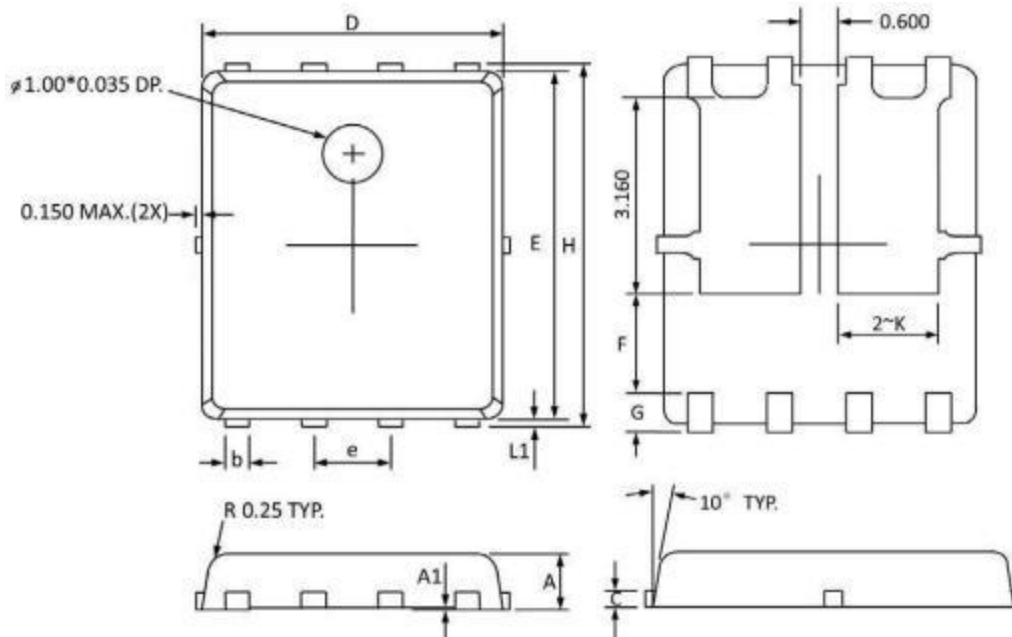


Figure 4: Diode Recovery Test Circuit & Waveform



**DFN5x6 PACKAGE INFORMATION**



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.800	1.000	0.032	0.039
A1	0.000	0.005	0.000	0.000
b	0.350	0.490	0.014	0.019
C	0.254 Ref		0.254 Ref	
D	4.900	5.100	0.193	0.200
E	5.700	5.900	0.225	0.232
e	1.27 BSC		1.27 BSC	
F	1.600 Ref		1.600 Ref	
G	0.600 Ref		0.600 Ref	
H	5.950	6.200	0.235	0.244
L1	0.100	0.180	0.004	0.007
K	1.600 Ref		1.600 Ref	



## **Disclaimer**

Brunei has made reasonable commercial efforts to ensure that the information given in this datasheet is correct. However, it must clearly be understood that such information is for guidance only and does not constitute any representation or form part of any offer or contract.

For documents and material available from this datasheet, Brunei does not warrant or assume any legal liability or responsibility for the accuracy, completeness, or usefulness of any information, product, technology or process disclosed hereunder.

Brunei reserves the rights to at its own discretion to make any changes or improvements to this datasheet. Unless said datasheet is incorporated into the formal contract, any customer should not rely on the information as any specification or product parameters duly committed by Brunei Customers are hereby advised to verify that the information contained herein is current and complete before the entering of any contract or acknowledgement of any purchase order. Accordingly, all products specified hereunder shall be sold subject to Brunei's terms and conditions supplied at the time of order acknowledgement. Except where agreed upon by contractual agreement, testing of all parameters of each product is not necessarily performed.

Brunei does not warrant or convey any license either expressed or implied under its patent rights, nor the rights of others. Reproduction of information contained herein shall be only permissible if such reproduction is without any modification or alteration. Reproduction of this information with any alteration is an unfair and deceptive business practice. Brunei is not responsible or liable for such altered documentation.

Resale of Brunei's products with statements different from or beyond the parameters stated by Brunei for that product or service voids all express or implied warranties for the associated Brunei's product or service and is unfair and deceptive business practice. Brunei is not responsible or liable for any such statements.

Brunei's products are not authorized for use as critical components in life support devices or systems without the express written approval of Brunei. As used herein:

1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body, or (b) support or sustain life, and whose failure to perform, when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in a significant injury to the user.
2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.